

The TDS4 is a medium voltage, high current, thin pack disc SCR employing an amplifying gate structure. This thin package provides greater cooling thus maximizing high current performance. The amplifying gate design allows the SCR to be reliably operated at high di/dt and dv/dt conditions in various phase control applications.

FEATURES:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Hermetic Ceramic Package
- Excellent Surge and I^2t Ratings

APPLICATIONS:

- DC Power Supplies
- Motor Controls
- Plating Rectifiers

ORDERING INFORMATION

Select the complete 12 digit Part Number using the table below.
 EXAMPLE: TDS4363402DH is a 3600V 3475A SCR with 300ma IGT and 12 inch gate and cathode potential leads.

PART	Voltage Rating $V_{DRM}-V_{RRM}$	Voltage Code	Current Rating I_{avg}	Current Code	Turn-Off T_q	Gate I_{GT}	Leads
TDS4	3600	36	3475	34	0	2	DH
	3400	34					
	3200	32			600us	300ma	12"
	3000	30			(typ.)	(max)	

Revised: 7/28/2020

Absolute Maximum Ratings

Characteristic	Symbol	Rating	Units
Repetitive Peak Voltage	$V_{DRM}-V_{RRM}$	3000 - 3600	Volts
Average On-State Current, $T_C=70^{\circ}C$	$I_{T(Avg.)}$	3475	A
RMS On-State Current, $T_C=70^{\circ}C$	$I_{T(RMS)}$	5459	A
Average On-State Current, $T_C=55^{\circ}C$	$I_{T(Avg.)}$	4040	A
RMS On-State Current, $T_C=55^{\circ}C$	$I_{T(RMS)}$	6346	A
Peak One Cycle Surge Current, 60Hz, $V_R=0V$	I_{TSM}	71,700	A
Peak One Cycle Surge Current, 50Hz, $V_R=0V$	I_{TSM}	67,200	A
Fuse Coordination I^2t , 60Hz	I^2t	2.14E+07	A ² s
Fuse Coordination I^2t , 50Hz	I^2t	2.26E+07	A ² s
Critical Rate-of-Rise of On-State Current	di/dt	100	A/us
Repetitive			
Critical Rate-of-Rise of On-State Current	di/dt	300	A/us
Non-Repetitive			
Peak Gate Power, 100us	P_{GM}	16	Watts
Average Gate Power	$P_{G(avg)}$	5	Watts
Operating Temperature	T_j	-40 to+125	$^{\circ}C$
Storage Temperature	$T_{Stg.}$	-50 to+150	$^{\circ}C$
Approximate Weight		4.7	lb
		2.13	Kg
Mounting Force		16,000-20,000	lbs
		71.2 - 89.0	KNewtons

Information presented is based upon manufacturers testing and projected capabilities. This information is subject to change without notice. The manufacturer makes no claim as to suitability for use, reliability, capability or future availability of this product.

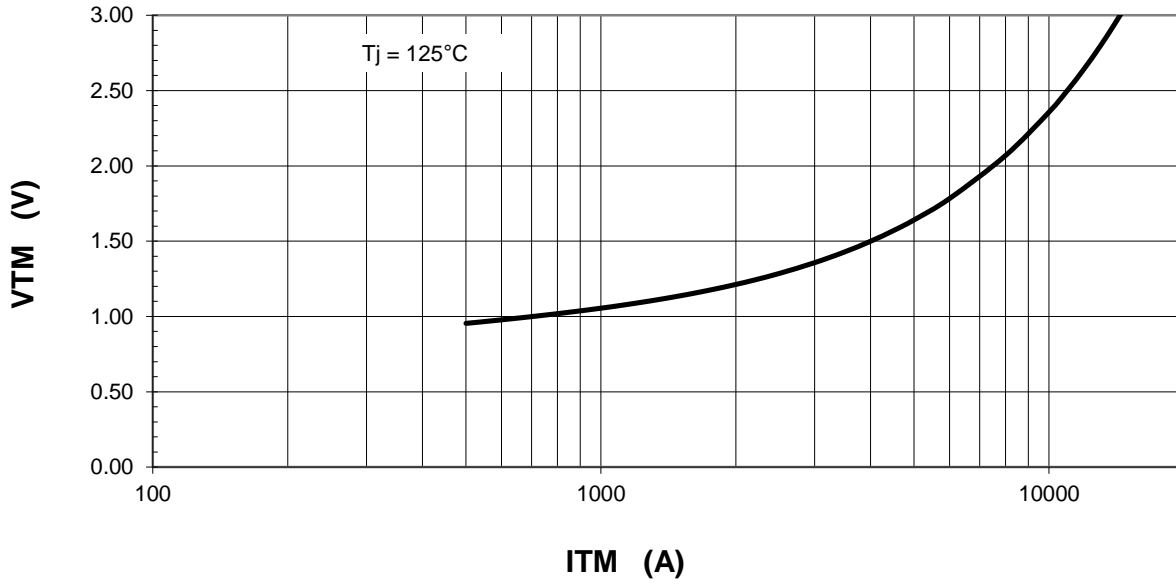
Electrical Characteristics, T_j=25°C unless otherwise specified

Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Repetitive Peak Forward Leakage Current	I _{DRM}	T _j =125°C, V _{DRM} =Rated			300	ma
Repetitive Peak Reverse Leakage Current	I _{RPM}	T _j =125°C, V _{RPM} =Rated			300	ma
Peak On-State Voltage	V _{TM}	T _j =125°C, I _{TM} =4000A			1.50	V
V _{TM} Model, Low Level	V ₀	T _j =125°C			0.914	V
V _{TM} = V ₀ + r•I _{TM}	r	15% I _{TM} - π•I _{TM}			0.145	mΩ
V _{TM} Model, High Level	V ₀	T _j =125°C			0.802	V
V _{TM} = V ₀ + r•I _{TM}	r	π•I _{TM} - I _{TSM}			0.152	mΩ
V _{TM} Model, 4-Term	A	T _j =125°C			0.285	
V _{TM} = A + B•Ln(I _{TM}) +	B	15%I _{TM} - I _{TSM}			0.120	
C•(I _{TM}) + D•(I _{TM}) ^½	C				1.69E-04	
	D				-7.20E-03	
Turn-On Delay Time	t _d	V _D = 0.5•V _{DRM} Gate Drive: 40V - 20Ω		3		us
Turn-Off Time	t _q	T _j =125°C dv/dt = 20V/us to 67% V _{DRM}			600	us
dv/dt _(Crit)	dv/dt	T _j =125°C Exp. Waveform V _D =67% Rated	1000			V/us
Gate Trigger Current	I _{GT}	T _j =25°C V _D = 12V	30	150	300	ma
Gate Trigger Voltage	V _{GT}		0.8	2.0	5.0	V
Peak Reverse Gate Voltage	V _{GRM}				5	V

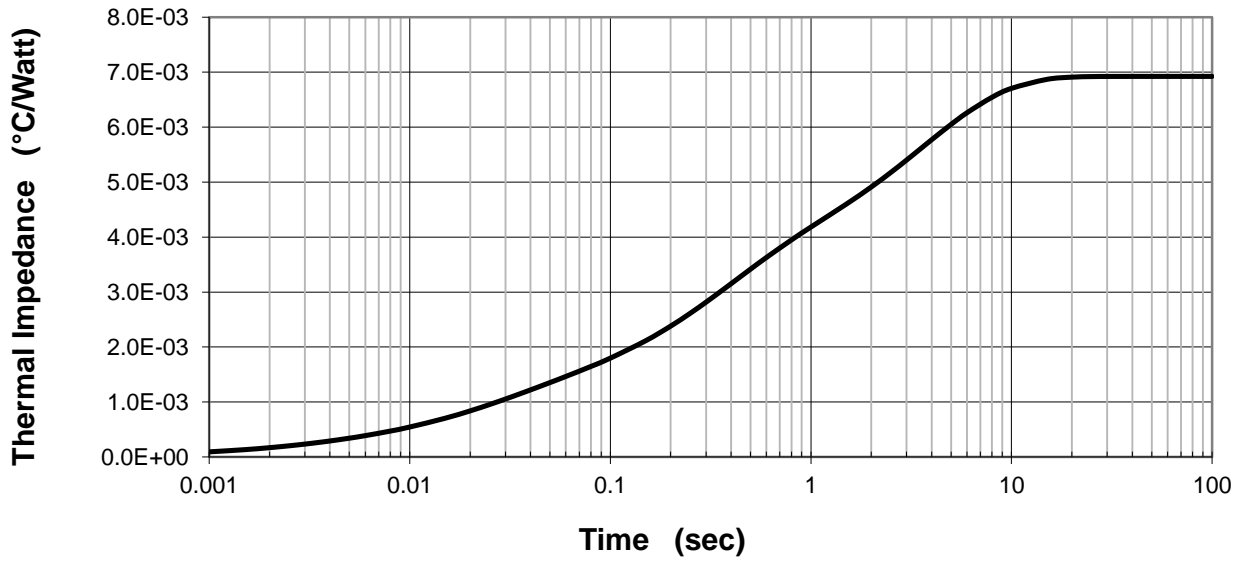
Thermal Characteristics

Characteristic	Symbol	Test Conditions	Rating				Units
			max				
Thermal Resistance							
Junction to Case	RΘ _{jc}	Double side cooled			0.0070	°C/Watt	
Case to Sink	RΘ _{cs}	Double side cooled			0.0015	°C/Watt	
Thermal Impedance Model							
ZΘ _{jc} (t) = Σ(A(N)•(1-exp(-t/Tau(N))))	ZΘ _{jc}	Double side cooled					
		where:	N =	1	2	3	4
			A(N) =	1.43E-04	9.08E-04	2.37E-03	3.50E-03
			Tau(N) =	2.62E-03	2.31E-02	3.05E-01	3.60E+00

Maximum On-State Voltage Drop

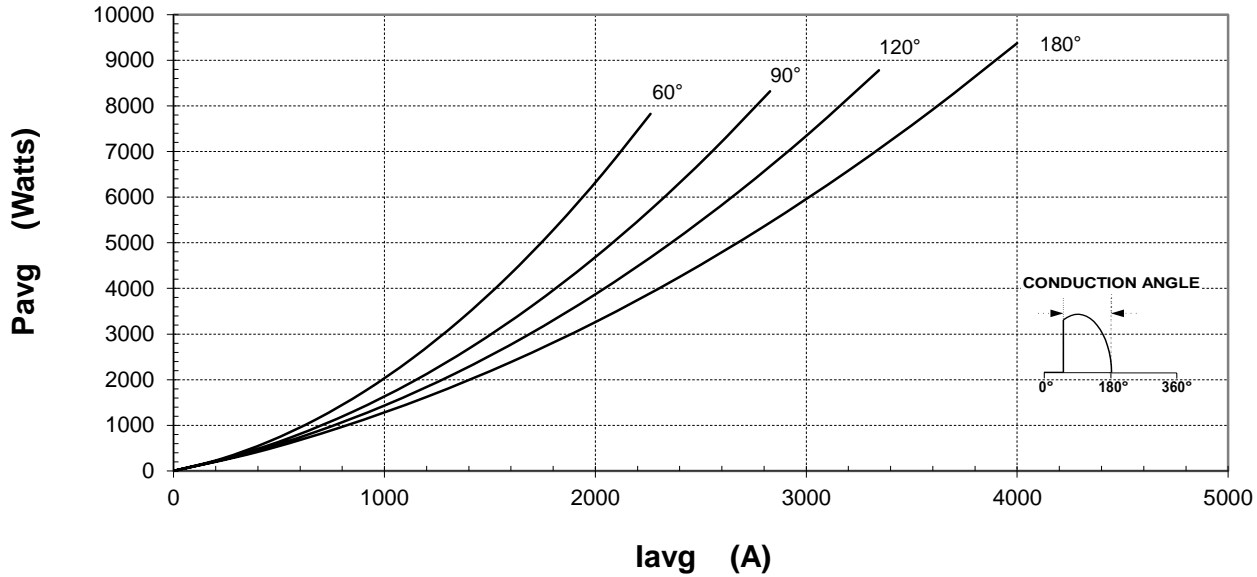


MAXIMUM TRANSIENT THERMAL IMPEDANCE



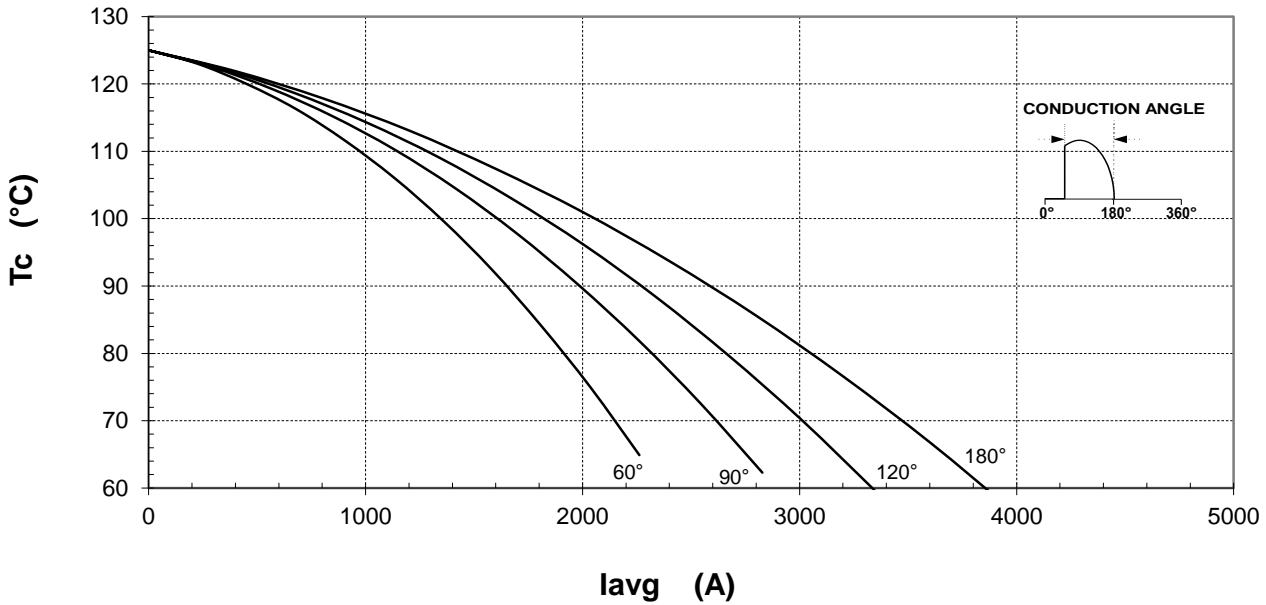
Maximum On-State Power Dissipation

Sinusoidal Waveform



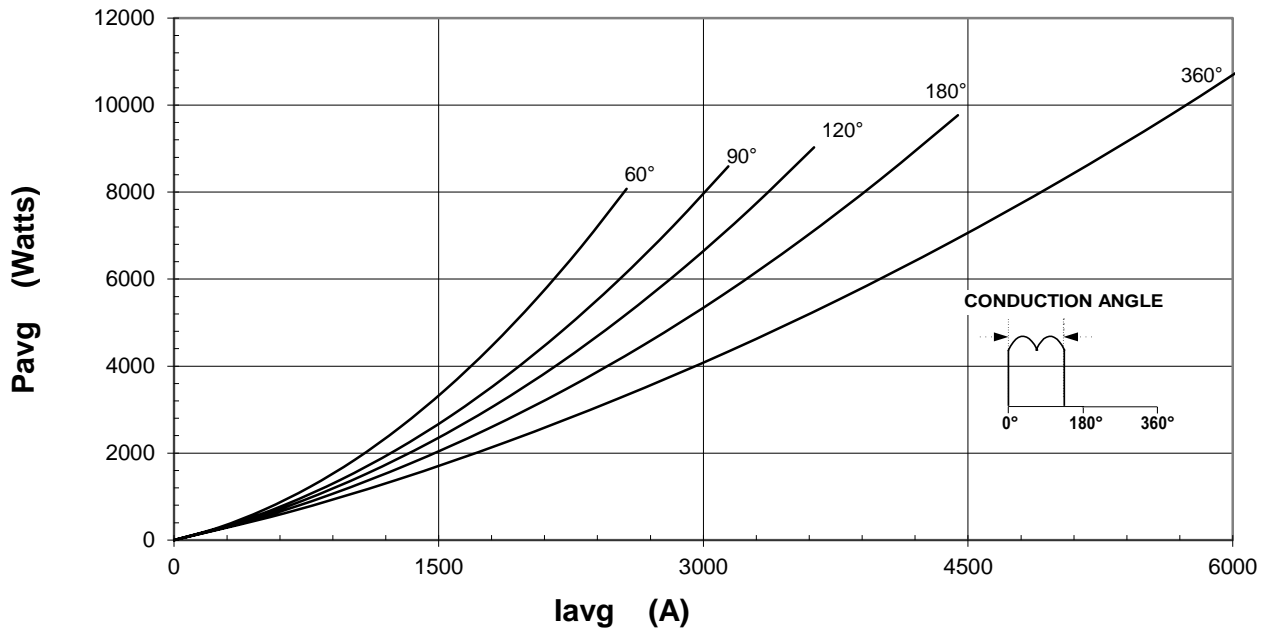
Maximum Allowable Case Temperature

Sinusoidal Waveform



Maximum On-State Power Dissipation

Square Waveform



Maximum Allowable Case Temperature

Square Waveform

